

**40V N-Channel Enhancement Mode MOSFET**

**MAIN CHARACTERISTICS**

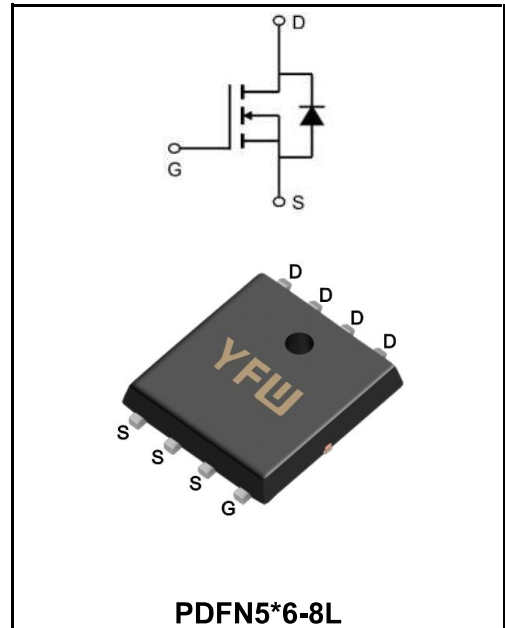
<b>I<sub>D</sub></b>	140A
<b>V<sub>DSS</sub></b>	40V
<b>R<sub>DS(on)-typ(@V<sub>GS</sub>=10V)</sub></b>	<2.7mΩ( <b>Typ:1.85 mΩ</b> )

**APPLICATIONS**

- ♣ Battery protection
- ♣ Load switch
- ♣ Uninterruptible power supply

**MECHANICAL DATA**

- ♣ Case: Molded plastic
- ♣ Mounting Position: Any
- ♣ Molded Plastic: UL Flammability Classification Rating 94V-0
- ♣ Lead free in compliance with EU RoHS 2011/65/EU directive
- ♣ Solder bath temperature 275°C maximum, 10s per JESD 22-B106



**Maximum Ratings at Tc=25°C unless otherwise specified**

Characteristics	Symbols	Value	Units
Drain-Source Voltage	<b>V<sub>DS</sub></b>	40	<b>V</b>
Gate - Source Voltage	<b>V<sub>GS</sub></b>	±20	<b>V</b>
Continue Drain Current	<b>I<sub>D</sub></b>	140	<b>A</b>
Pulsed Drain Current (Note1)	<b>I<sub>DM</sub></b>	380	<b>A</b>
Single Pulse Avalanche Energy (Note1)	<b>E<sub>AS</sub></b>	500	<b>mJ</b>
Total Power Dissipation	<b>P<sub>D</sub></b>	96	<b>W</b>
Storage Temperature Range	<b>T<sub>STG</sub></b>	-55 to +150	<b>°C</b>
Operating Junction Temperature Range	<b>T<sub>J</sub></b>	150	<b>°C</b>
Thermal Resistance, Junction to Ambient	<b>R<sub>θJA</sub></b>	62	<b>°C/W</b>
Thermal Resistance, Junction to Case	<b>R<sub>θJC</sub></b>	1.3	<b>°C/W</b>

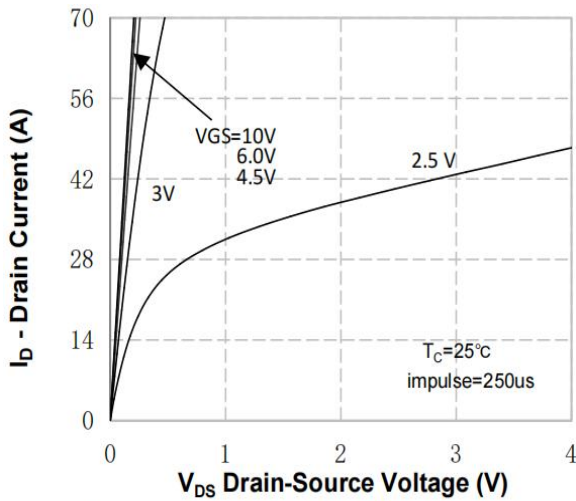
Note1:Pulse test: 300 μs pulse width, 2 % duty cycle

**Maximum Ratings at Tc=25°C unless otherwise specified**

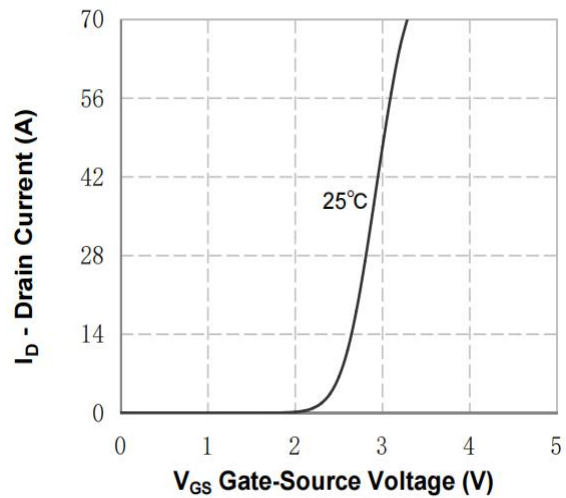
Characteristics	Test Condition	Symbols	Min	Typ	Max	Units
Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	$BV_{DSS}$	40	-	-	V
Gate Body Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	$I_{GSS}$	-	-	$\pm 100$	nA
Drain-Source Leakage Current	$V_{DS} = 40 V, V_{GS} = 0 V$	$I_{DSS}$	-	-	1	$\mu A$
Gate Threshold Voltage	$V_{DS}=V_{GS}, I_D=250\mu A$	$V_{GS(th)}$	1	-	2.2	V
Drain-Source on-Resistance (Note 2)	$V_{GS}=10V, I_D=20A$	$R_{DS(on)}$	-	1.85	2.7	m $\Omega$
	$V_{GS}=4.5V, I_D=15A$		-	2.5	3.5	m $\Omega$
Input Capacitance	$V_{DS}=25V$ $V_{GS}=0V$ $f=1MHz$	$C_{iss}$	-	7800	-	$\mu F$
Output Capacitance		$C_{oss}$	-	1256	-	
Reverse Transfer Capacitance		$C_{rss}$	-	780	-	
Total Gate Charge (Note 2)	$V_{GS}=4.5V$ $V_{DS}=20V$ $I_D=70A$	$Q_g$	-	170	-	nC
Gate-Source Charge (Note 2)		$Q_{gs}$	-	52	-	
Gate-Drain Charge (Note 2)		$Q_{gd}$	-	70	-	
Turn-on delay time (Note 2)	$V_{DD}=20 V$ $V_{GS}=10 V,$ $RG=3.7 \Omega$ $ID=70A$	$t_{d(on)}$	-	25	-	ns
Rise Time (Note 2)		$T_r$	-	80	-	
Turn-Off Delay Time (Note 2)		$t_{d(OFF)}$	-	85	-	
Fall Time (Note 2)		$t_f$	-	42	-	
Body Diode Reverse Recovery Time(Note2)	$T_J = 25^\circ C, I_F= 40A$ $di / dt = 100 A/\mu s$	$t_{rr}$	-	31	-	ns
Body Diode Reverse Recovery Charge(Note2)		$Q_{rr}$	-	27	-	nC
Drain-Source Diode Forward Voltage	$V_{GS}=0V, I_S=20A, T_J=25^\circ C$	$V_{SD}$	-	-	1.2	V
Maximun Body-Diode Continuous Current		$I_S$	-	-	140	A

Note2:Pulse test: 300  $\mu s$  pulse width, 2 % duty cycle

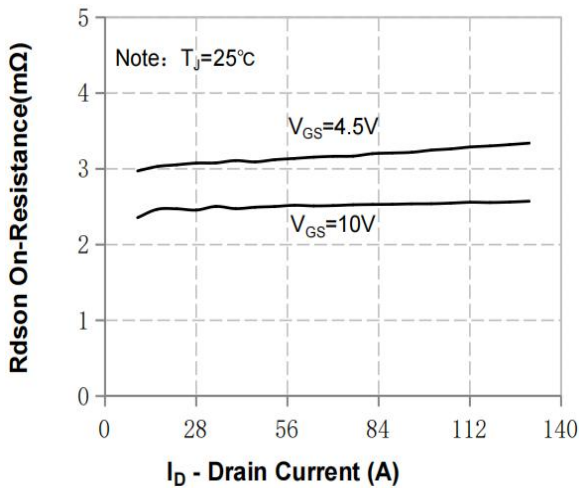
**Ratings and Characteristic Curves**



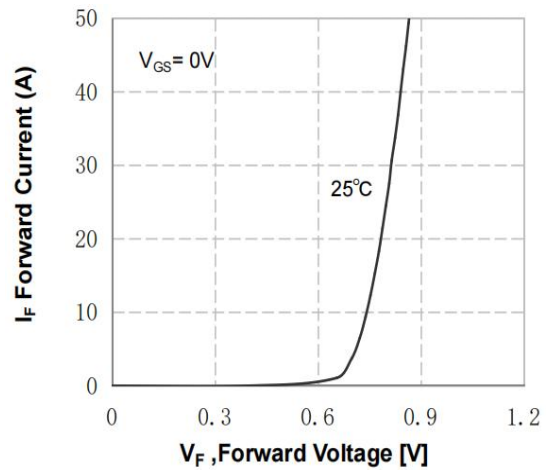
**Figure 1. On-Region Characteristics**



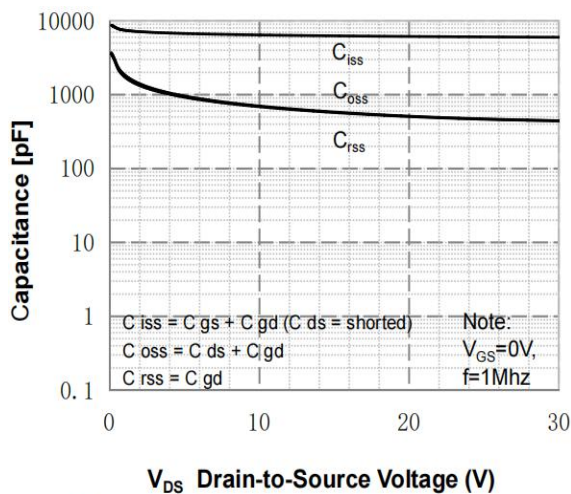
**Figure 2. Transfer Characteristics**



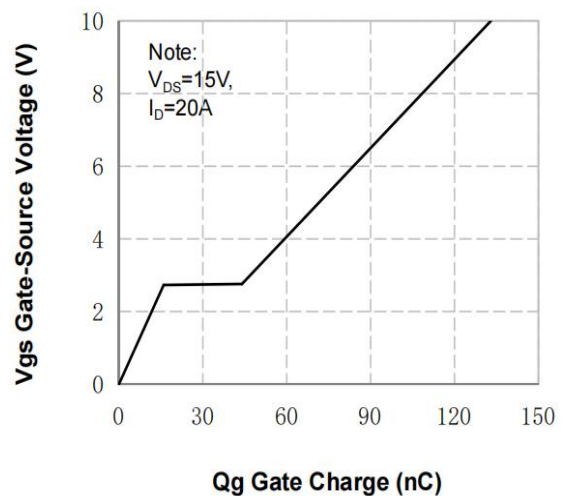
**Figure 3. On-Resistance Variation vs Drain Current and Gate Voltage**



**Figure 4. Body Diode Forward Voltage Variation with Source Current and Temperature**



**Figure 5. Capacitance Characteristics**



**Figure 6. Gate Charge Characteristics**

Ratings and Characteristic Curves

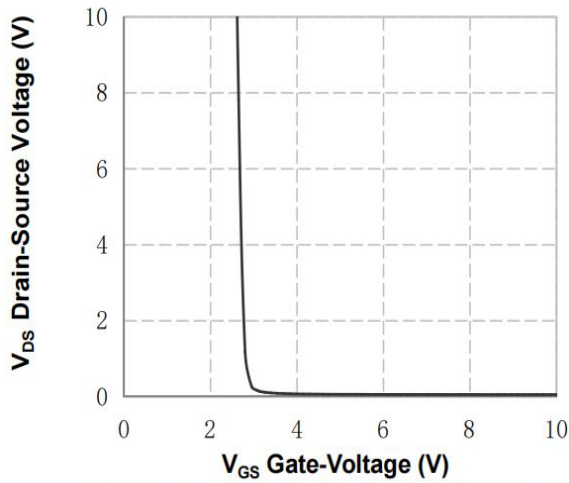


Figure 7. Vds Drain-Source Voltage vs Gate Voltage

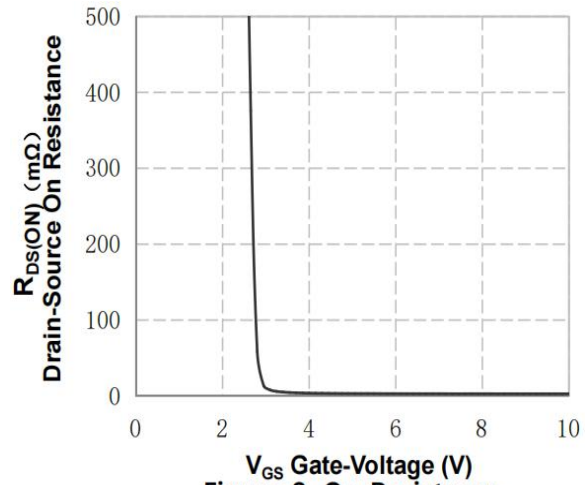


Figure 8. On-Resistance vs Gate Voltage

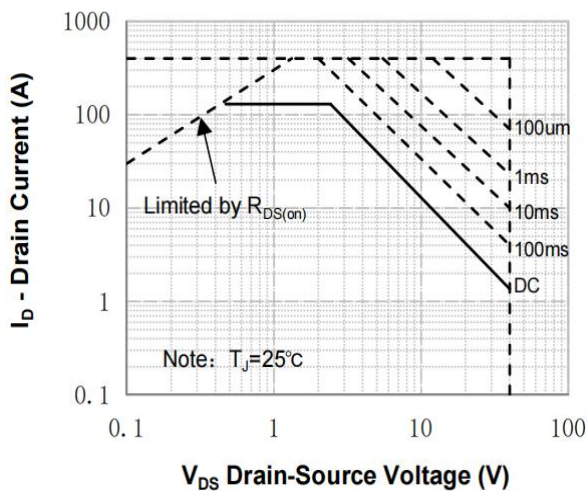


Figure 9. Maximum Safe Operating Area

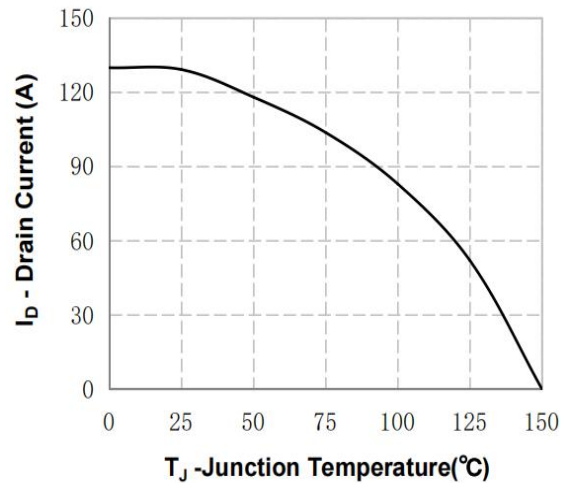


Figure 10. Maximum Continuous Drain Current vs Case Temperature

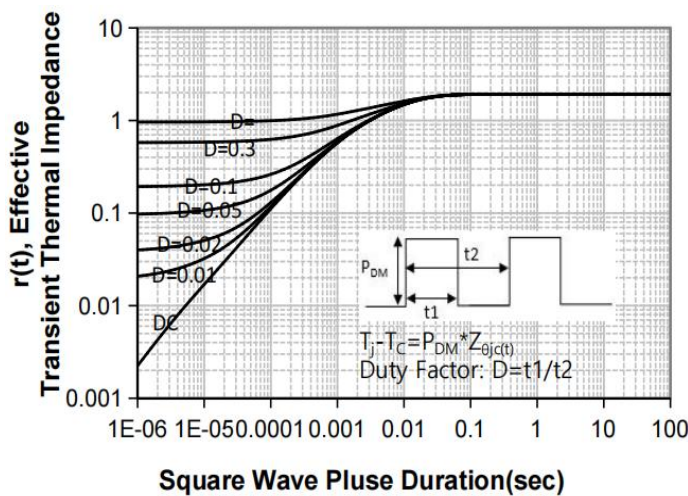
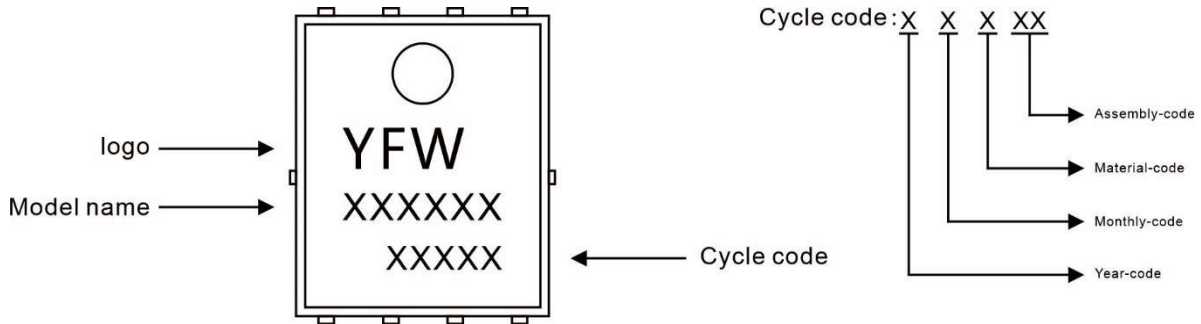


Figure 11. Transient Thermal Response Curve

**Marking Diagram**



**Ordering information**

Model name	Package	Unit Weight	Base Quantity	Packing Quantity
YFW140N04NF	PDFN5*6-8L	0.0032oz(0.093g)	5000pcs/reel	10000pcs/box 50000pcs/Carton

**Package Dimensions**

PDFN5\*6-8L

Dim	Millimeter		mil	
	Min.	Max.	Min.	Max.
A	0.9	1.2	35	45
A2	0.204	0.304	8	12
b	0.4ref.		16ref.	
b1	0.2	0.4	8	16
D	5.0	5.3	197	209
D1	4.84	5.24	191	206
E	5.95	6.35	234	250
E1	3.275	3.675	129	145
E2	5.69	6.09	224	232
e	1.27typ.		50typ.	
K	1.29typ.		51typ.	
L	0.585	0.785	23	27
L1	0.7typ.		28typ.	

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